PCN Number:	202	20615006	5.2		PCN Da	ate: J	lune 16, 2022	
							logy, Die Revision,	
Customer Cont		PCN Man		bly site/BOM c	Deptions fo		2903QDGKRQ1 Quality Services	
Proposed 1 st Sł		Dec 13, 2			e requests	-	luly 17, 2022	
*Sample reque	sts received	after Jul	y 17, 20			orted.		
Change Type:								
Assembly Si	te		embly Pr		\square		oly Materials	
Design				ecification			nical Specification	
Test Site	Cito			pping/Labeling		Test Pro		
Wafer Bump			er Fab M	Material			Bump Process Fab Process	
	iic			bolization		Walchi	401100035	
				Details				
Description of	Change:							
Texas Instrumen (CFAB, JI3), die Construction diff	revision, final erences are n	test site, oted belov	and Asse		site for th	e LM290	3QDGKRQ1.	
	urrent Fab S				New	/ Fab Sit		
Current Fab	Process	-	fer	New Fab	Pr	ocess	Wafer	
Site SFAB	JI1		n eter mm	Site CFAB		JI3	200 mm	
The die was also	-					712	200 11111	
Probe site chang	e: & Final Test	TI SH	Current:	obe (SH-BIP) 8			New: /a & HFTFAT	
11000 010		110						
Construction diff	erences are n	oted belov		urrent – ASE	SH	Add	itional -	
							HFTF	
	ompound		S	SID#EN20007				
	vire diameter Compound		Au, 1.0 mils					
	otective Layer		SID#EY100006 Nitride			Oxide, Nitride		
Package Marking				- Hichde		- Child	c, manao	
0	·		Current			Addi	itional	
Top Side	YM TI Device 0		YMLL Device					
	TI	= TI CHARA			VM - VE	DATE CODE		

Test coverage, insertions, conditions will remain consistent with current testing and verified with test $\ensuremath{\mathsf{MQ}}$

Reason for Change:

These changes are part of our multiyear plan to transition products from our 150-milimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
🛛 No Change	🛛 No Change	🛛 No Change	🛛 No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
SH-BIP-1	SHE	USA	Sherman
CFAB	CU3	CHN	Chengdu

Die Rev:

Current	New
Die Rev [2P]	Die Rev [2P]
A	Α

Assembly Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
ASESH	ASH	CHN	Shanghai
HFTF	HFT	CHN	Hefei

Sample product shipping label (not actual product label)

TEXAS INSTRUMENTS MADE IN: Malaysia 20C: 20: MSL 2 /260C/1 YEAR SEAL DT 03/29/04 OPT: ITEM: 39 LBL: 5A (L)T0:1750	(1P) SN74LSO7NSR (Q) 2000 (D) 0336 (31T) LOT: 3959047MLA (4W) TKY (1T) 7523483SI2 (P) (2P) REV: (V) 0033317 (20L) 050: SHE (21L) 00033317 (20L) 050: SHE (21L) 00033317 (20L) 050: SHE (21L) 00033317 (20L) 050: SHE (21L) 00033317
Product Affected:	
LM2903QDGKRQ1	



Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

LM2903QDGKRQ1 Approve Date 17-FEBRUARY -2022

Product Attributes

Attributoo	Qual Device:	QBS Product Reference:	QBS Process Reference:
Attributes	LM2903QDGKRQ1	LM2903BQDRQ1	LM2904BQDRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Signal Chain	Signal Chain	Signal Chain
Wafer Fab Supplier	CFAB	CFAB	CFAB
Assembly Site	HFTFAT	FMX	FMX
Package Group	VSSOP	SOIC	SOIC
Package Designator	DGK	D	D
Pin Count	8	8	8

QBS: Qual By Similarity

Qual Device LM2903QDGKRQ1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot	SS / Lot	Test Name	Condition	Duration	Qual Device: LM2903QDGKRQ1	QBS Product Reference:	QBS Process Reference:			
			Qty					LW2903QDGKKQI	LM2903BQDRQ1	LM2904BQDRQ1			
Test Group	est Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	MSL1 260C	1 Step	3/924/0	-	-			
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	110C/85%RH	264 Hours	3/231/0	-	-			
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	3/231/0	-	-			
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	1000 Cycles	3/231/0	-	-			
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/72/0	-	-			
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	3/231/0	-	-			
Test Group	B - Acce	elerated Lifetime Sin	ulation	Tests									
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	150C	300 Hours	1/77/0	3/231/0	-			
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	150C	408 Hours	-	-	3/231/0			
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	-	1/800/0	3/2400/4 ¹			
Test Group	C - Pack	age Assembly Integ	rity Tes	ts									
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/300/0	-	-			

WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/300/0	-	-
SD	СЗ	JEDEC JESD22- B102	1	15	PB Solderability	>95% Lead Coverage	-	1/15/0	-	-
SD	СЗ	JEDEC JESD22- B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	1/15/0	-	-
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	3/30/0	-	-
Test Group	D - Die F	abrication Reliability	y Tests							
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	-	-
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	-	-
НСІ	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	-	-
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	-	-
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	-	-
Test Group	E - Elect	rical Verification Tes	sts							
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	-	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	1500 Volts	1/3/0	-	-
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100- 004	-	1/6/0	-	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	-	-

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2110-016

[Note1]- ELFR fails due to a defect screenable at production test.



Automotive New Product Qualification Summary (As per AEC-Q100/Q006 and JEDEC Guidelines)

Q006 Summary for 0.8 PCC Wire JI3 AL Bond Pads in HFTF (Grade 1, -40/125C)

Approved 02-Jul-2021

Product Attributes

Attributes	Qual Device: <u>LM2903BQDGKRQ1</u>
Automotive Grade Level	Grade 1
Operating Temp Range (C)	-40 to 125
Product Function	Signal Chain
Wafer Fab Supplier	CFAB
Assembly Site	HFTFAT
Package Group	VSSOP
Package Designator	DGK
Ball/Lead Count	8

- QBS: Qual By Similarity

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>LM2903BQDGKRQ1</u>
		Test Grou	p A – Accelerate	d Environn	nent Stress Tests		
PC	A1	-	3	22	SAM Analysis, Pre Stress	Completed	3/66/0
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	Level 1-260C	3/924/0
PC	A1	-	3	22	SAM Analysis, Post Stress	Completed	3/66/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 110C/85%RH	264 Hours	3/231/0
HAST	A2	-	3	1	Cross Section, Post bHAST 264 Hours	-	-
HAST	A2	-	3	30	Wire Bond Shear, Post bHast, 264 Hours	Wires	-
HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 264 Hours	Wires	-
HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 264 Hours	Wires	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 110C/85%RH	528 Hours	3/210/0
HAST	A2	-	3	1	Cross Section, Post bHAST 528 Hours	Completed	3/3/0
HAST	A2	-	3	22	SAM Analysis, Post bHAST, 528 Hours	Completed	3/66/0
HAST	A2	-	3	30	Wire Bond Shear, Post bHast, 528 Hours	Wires	3/24/0
HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 528 Hours	Wires	3/24/0
HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 528 Hours	Wires	3/24/0
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0
тс	A4	-	3	1	Cross Section, Post T/C 500 Cycles	-	-
тс	A4	-	3	22	SAM Analysis, Post T/C, 500 Cycles	Completed	3/66/0
тс	A4	-	3	30	Wire Bond Shear, Post T/C 500 Cycles	Wires	-
тс	A4	-	3	30	Bond Pull over Stitch Post T/C 500 Cycles	Wires	-
тс	A4	-	3	30	Bond Pull over Ball Post T/C 500 Cycles	Wires	-
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	1000 Cycles	3/210/0

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

	Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LM2903BQDGKRQ1	
	тс	A4	-	3	1	Cross Section, Post T/C 1000 Cycles	Completed	3/3/0	
	тс	A4	-	3	22	SAM Analysis, Post T/C, 1000 Cycles	Completed	3/66/0	
	TC	A4	-	3	30	Wire Bond Shear, Post T/C 1000 Cycles	Wires	3/24/0	
	тс	A4	-	3	30	Bond Pull over Stitch, Post T/C, 1000 Cycles	Wires	3/24/0	
	тс	A4	-	3	30	Bond Pull over Ball, Post T/C, 1000 Cycles	Wires	3/24/0	
	PTC	A 5	JEDEC JESD22-A105	1	45	Power Temperature Cycle -40/125C	1000 Cycles	-	
	PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle -40/125C	2000 Cycles	-	
	HTSL	A6	JEDEC JESD22-A103	3	45	High Temp Storage Bake 150C	1000 Hours	3/231/0	
	HTSL	A 6	-	3	1	Cross Section, Post HTSL 1000 Hours	-	-	
	HTSL	A6	JEDEC JESD22-A103	3	44	High Temp Storage Bake 150C	2000 Hours	3/228/0	
	HTSL	A6	-	3	1	Cross Section, Post HTSL 2000 Hours	Completed	3/3/0	
Test Group C – Package Assembly Integrity Tests									
	WBS	C1	AEC Q100-001	3	30	Wire Bond Shear, Cpk>1.67	Wires	3/300/0	
	WBP	C2	MIL-STD883 Method 2011	3	30	Bond Pull over Ball, Cpk >1.67	Wires	3/300/0	

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST & TC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40C to +150C Grade 1 (or Q): -40C to +125C Grade 2 (or T): -40C to +105C Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold : HTOL, ED Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room : AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20190802-130791

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail
WW Change Management Team	PCN ww admin team@list.ti.com

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